

Abstracts

60W L-band power AlGaAs/GaAs heterostructure FETs

J. Morikawa, K. Asano, K. Ishikura, H. Oikawa, M. Kanamori and M. Kuzuhara. "60W L-band power AlGaAs/GaAs heterostructure FETs." 1997 MTT-S International Microwave Symposium Digest 3. (1997 Vol. III [MWSYM]): 1413-1416.

This paper describes DC and RF power performance of a newly-developed high-power AlGaAs/GaAs heterostructure FET (HFET) designed for L-band SSPA applications. A push-pull power amplifier, composed of two HFET chips, demonstrated state-of-the-art power performance of 60 W output-power with a power-added efficiency (PAE) of 54% at 1.5 GHz.

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